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L1 192227 S SEMICONDUCTOR? OR SILICON OR SI  
L2 13302 S (IMPURITIES OR IMPURITY) AND CARBON AND NITROGEN AND OXY  
GEN  
L3 5268 S L1 AND L2  
L4 1467 S L3 AND AMORPHOUS  
L5 125 S L4 AND RECRYSTAL?  
L6 0 S L5 AND CCLS/257  
L7 0 S 257/CCLR  
L8 9 S L5 AND (THIN FILM)

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  2. 5,123,975, Jun. 23, 1992, Single crystal silicon substrate; Mitsugu Irinoda, et al., 148/33.2, 33.3; 156/603, 604; 437/46, 62, 83, 84, 174, 233, 973 [IMAGE AVAILABLE]
  3. 5,117,057, May 26, 1992, Insecticidal N' substituted-N-N'-disubstituted-hydrazines; Adam C. Hsu, et al., 564/149; 544/224, 335, 406; 546/316, 324, 325, 332; 548/213, 214, 238, 248, 255, 537, 563; 549/65, 72, 436, 484, 487, 494, 496, 553; 556/419; 558/6, 10, 17, 58, 273, 275, 404, 415; 560/27, 29, 30, 34, 138, 163, 221, 251; 564/12, 35, 36, 74, 81, 148, 150, 151 [IMAGE AVAILABLE]
  4. 5,108,843, Apr. 28, 1992, Thin film semiconductor and process for producing the same; Kouichi Ohtaka, et al., 428/446, 212, 428, 698, 699, 701, 704 [IMAGE AVAILABLE]
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  6. 4,916,470, Apr. 10, 1990, Image bar with electrochromic switching system; Gregory J. Kovacs, et al., 346/160, 155 [IMAGE AVAILABLE]
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51. 4,814,292, Mar. 21, 1989, Process of fabricating a semiconductor device involving densification and recrystallization of amorphous silicon; Masayoshi Sasaki, et al., 437/101; 148/DIG.1; 437/40, 83, 84, 233, 247, 248
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US PAT NO:  
TITLE:

4,814,292

Process of fabricating a semiconductor device

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